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RFMD(R) Announces Qualification of Second Gallium Nitride (GaN) Process Technology

RFMD to Highlight GaN Technology in Presentations at Upcoming Industry Conferences

GREENSBORO, N.C., May 10, 2010 (GlobeNewswire via COMTEX News Network) -- RF Micro Devices, Inc. (Nasdaq:RFMD), a global leader in the design and manufacture of high-performance RF components and compound semiconductor technologies, today announced the successful qualification of RFMD's second high-power Gallium Nitride (GaN) process technology, expanding the Company's industry-leading portfolio of compound semiconductor technologies.

RFMD's second high-power GaN HEMT process technology (GaN2) achieves 1-2dB higher gain and 6dB greater linearity than RFMD's first high-power GaN process technology (GaN1) at moderately lower power density. RFMD's GaN2 targets CATV broadband transmission products and other multi-market applications and is optimized for higher linearity, higher gain and lower voltage operation. RFMD's first high-power GaN process technology (GaN1) was qualified in the June 2009 quarter and delivers much higher power density and voltage breakdown than competing technologies. RFMD's GaN1 is ideally suited for high-performance devices such as power amplifiers for radar and communications.

RFMD's GaN2 reliability measurements confirm a useful lifetime of over 17 million hours at a channel temperature of 200 deg C. This industry-leading reliability performance is especially noteworthy because GaN2 is an early stage process on RFMD's GaN technology development roadmap. Additional technologies in development include MMIC process modules with complimentary Integrated Passive Component (IPC) technology.

Bob Van Buskirk, president of RFMD's Multi-Market Products Group (MPG), said, "RFMD's high-performance GaN technology is consistently demonstrating industry-leading levels of reliability, allowing our customers to design GaN products that exceed their stringent system reliability specifications. RFMD's GaN technology also enables advanced RF components and products that operate at significantly lower power consumption levels, helping to satisfy the rapidly increasing end-market requirements for energy saving 'green technologies.'"

RFMD is scheduled to present numerous white papers on GaN technology and product development at the upcoming Compound Semiconductor Mantech and IEEE MTT International Microwave Symposium conferences. Scheduled presentations include: "GaN Applications Beyond the PA for RF Systems," "GaN for High Power, High Bandwidth Applications," "Defining Application Spaces for High Power GaN," and "RFMD Takes GaN Mainstream." Industry participants interested in learning more about RFMD's GaN technology development roadmap can visit RFMD at Compound Semiconductor Mantech, in Portland, Oregon, on May 17-20, 2010, and at the IEEE MTT International Microwave Symposium, in Anaheim, California, on May 25-27, 2010. For more information please visit www.rfmd.com/foundry or email RFMDFoundryServices@rfmd.com.

About RFMD

RF Micro Devices, Inc. (Nasdaq:RFMD) is a global leader in the design and manufacture of high-performance radio frequency components and compound semiconductor technologies. RFMD's products enable worldwide mobility, provide enhanced connectivity and support advanced functionality in the cellular handset, wireless infrastructure, wireless local area network (WLAN), CATV/broadband and aerospace and defense markets. RFMD is recognized for its diverse portfolio of semiconductor technologies and RF systems expertise and is a preferred supplier to the world's leading mobile device, customer premises and communications equipment providers.

Headquartered in Greensboro, N.C., RFMD is an ISO 9001- and ISO 14001-certified manufacturer with worldwide engineering, design, sales and service facilities. RFMD is traded on the NASDAQ Global Select Market under the symbol RFMD. For more information, please visit RFMD's web site at www.rfmd.com.

The RF Micro Devices, Inc. logo is available at http://www.globenewswire.com/newsroom/prs/?pkgid=6436

This press release includes "forward-looking statements" within the meaning of the safe harbor provisions of the Private Securities Litigation Reform Act of 1995. These forward-looking statements include, but are not limited to, statements about our plans, objectives, representations and contentions and are not historical facts and typically are identified by use of terms such as "may," "will," "should," "could," "expect," "plan," "anticipate," "believe," "estimate," "predict," "potential," "continue" and similar words, although some forward-looking statements are expressed differently. You should be aware that the forward-looking statements included herein represent management's current judgment and expectations, but our actual results, events and

performance could differ materially from those expressed or implied by forward-looking statements. We do not intend to update any of these forward-looking statements or publicly announce the results of any revisions to these forward-looking statements, other than as is required under the federal securities laws. RF Micro Devices' business is subject to numerous risks and uncertainties, including risks associated with the impact of global macroeconomic and credit conditions on our business and the business of our suppliers and customers, variability in operating results, the rate of growth and development of wireless markets, our reliance on inclusion in third party reference designs for a portion of our revenue, our ability to manage channel partner and customer relationships, risks associated with the operation of our wafer fabrication, molecular beam epitaxy, assembly and test and tape and reel facilities, our ability to complete acquisitions and integrate acquired companies, including the risk that we may not realize expected synergies from our business combinations, our ability to attract and retain skilled personnel and develop leaders, variability in production yields, raw material costs and availability, our ability to reduce costs and improve margins in response to declining average selling prices, our ability to bring new products to market, our ability to adjust production capacity in a timely fashion in response to changes in demand for our products, dependence on a limited number of customers, dependence on gallium arsenide (GaAs) for the majority of our products, and dependence on third parties. These and other risks and uncertainties, which are described in more detail in RF Micro Devices' most recent Annual Report on Form 10-K and other reports and statements filed with the Securities and Exchange Commission, could cause actual results and developments to be materially different from those expressed or implied by any of these forward-looking statements.

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